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# N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)	
150	0.0076 at V <sub>GS</sub> = 10 V	110	63 nC	
	0.0081 at V <sub>GS</sub> = 7.5 V	100	03 110	

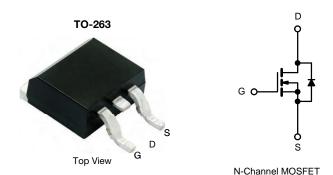
### **FEATURES**

- DT-Trench Power MOSFET
- Maximum 175 °C junction temperature
- 100 % R<sub>g</sub> and UIS tested



#### **APPLICATIONS**

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier
- · Battery management



<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	150	V			
Gate-Source Voltage		V <sub>GS</sub>	± 20	ľ		
Continuous Dunin Comment /T. 150 °C)	T <sub>C</sub> = 25 °C		110			
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 125 °C	I <sub>D</sub>	74			
Pulsed Drain Current (t = 100 μs)		I <sub>DM</sub>	330	A		
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	60			
Single Avalanche Energy <sup>a</sup>	L = 0.1 IIII	E <sub>AS</sub>	180	mJ		
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	375 <sup>b</sup>	W		
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	125 <sup>b</sup>			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W	
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.4		

#### Notes

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•		
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	5	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V	-	-	1	μА
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	100	
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	2	mA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	90	-	-	Α
5 . 6 . 6 . 6	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.0076	0.0084	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 7.5 \text{ V}, I_D = 10 \text{ A}$	-	0.0081	0.0089	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A	-	52	-	S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 75 V, f = 1 MHz	-	4225	-	pF
Output Capacitance	C <sub>oss</sub>		-	535	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	26	-	
Total Gate Charge <sup>c</sup>	$Q_{g}$		-	63	95	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	19.5	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	20.5	-	
Gate Resistance	$R_{g}$	f = 1 MHz	1.5	3	5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	15	30	ns
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 75 \text{ V}, R_L = 1.25 \Omega$	-	114	220	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	28	56	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	8	16	
Drain-Source Body Diode Ratings a	nd Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)				
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	330	Α
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.73	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs	-	110	220	ns
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>		-	10	20	Α
Reverse Recovery Charge	Q <sub>rr</sub>		-	0.5	1	μC

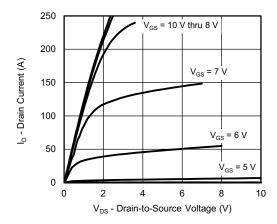
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

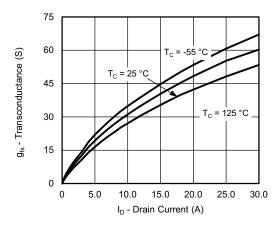
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



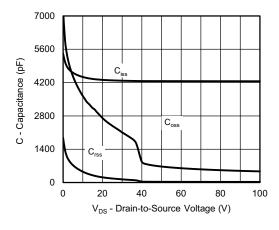
### **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



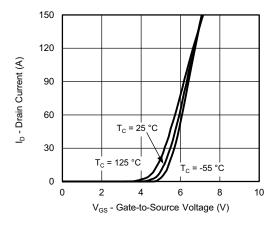
#### **Output Characteristics**



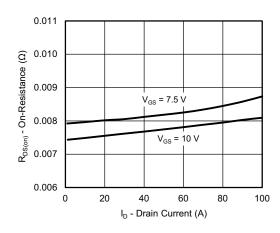
Transconductance



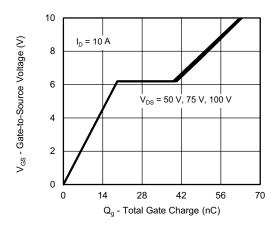
Capacitance



**Transfer Characteristics** 



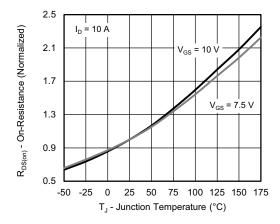
On-Resistance vs. Drain Current



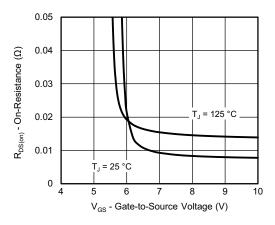
**Gate Charge** 



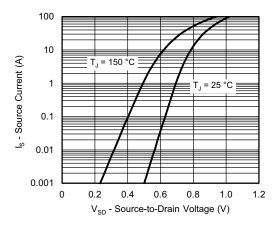
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



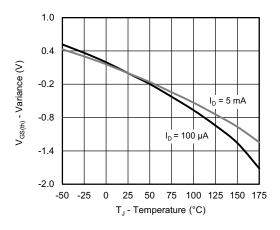
On-Resistance vs. Junction Temperature



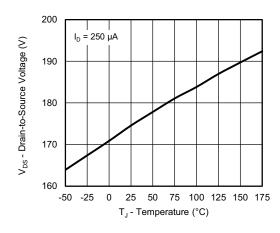
On-Resistance vs. Gate-to-Source Voltage



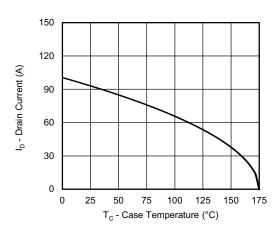
**Source Drain Diode Forward Voltage** 



Threshold Voltage



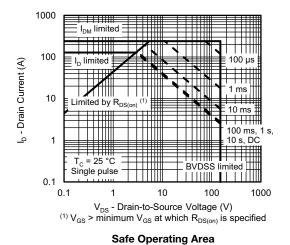
**Drain Source Breakdown vs. Junction Temperature** 

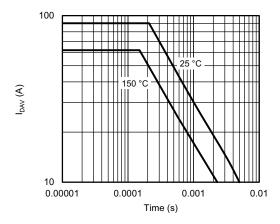


**Current De-Rating** 

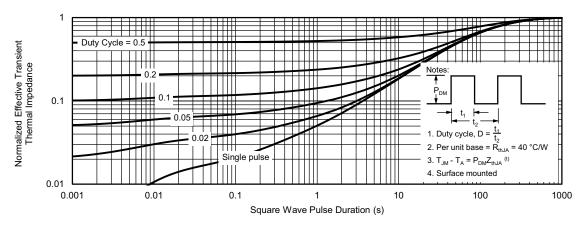


### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)





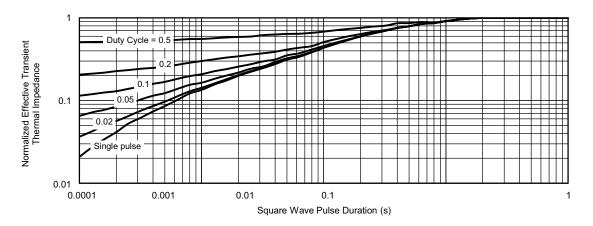
 $I_{\text{DAV}}$  vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient

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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.





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